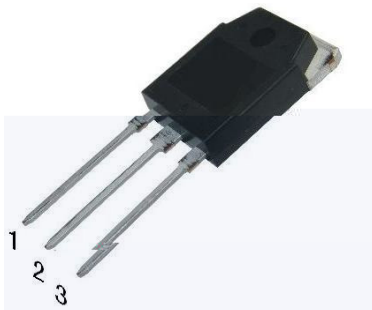
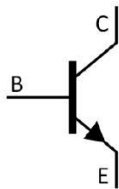


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Silicon NPN transistor in a TO-3P Plastic Package.

Recommend for 100W high fidelity audio frequency amplifier output stage, Complementary to 2SA1943.

Power amplifier applications.



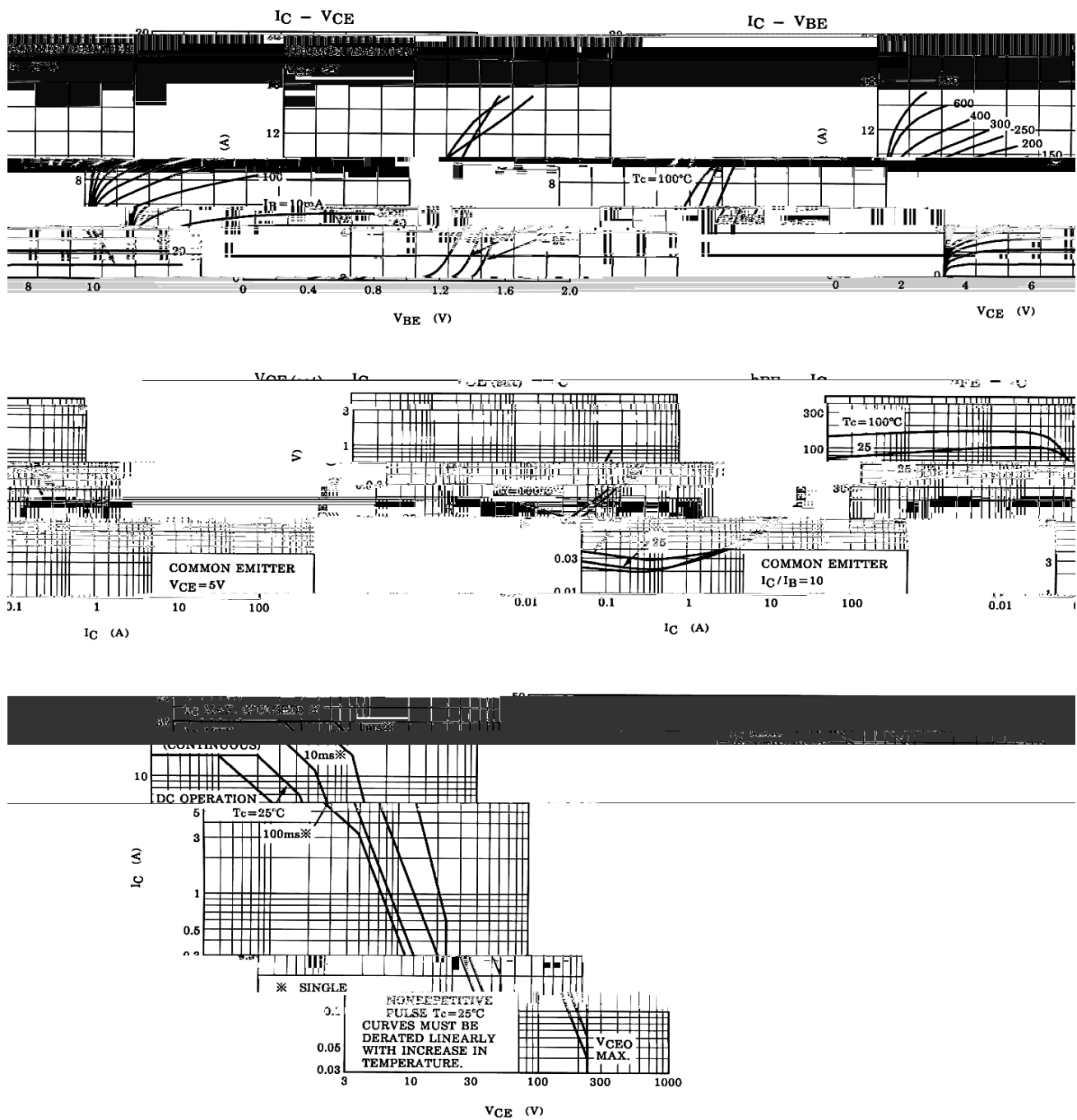
PIN1 Base PIN 2 Collector PIN 3 Emitter

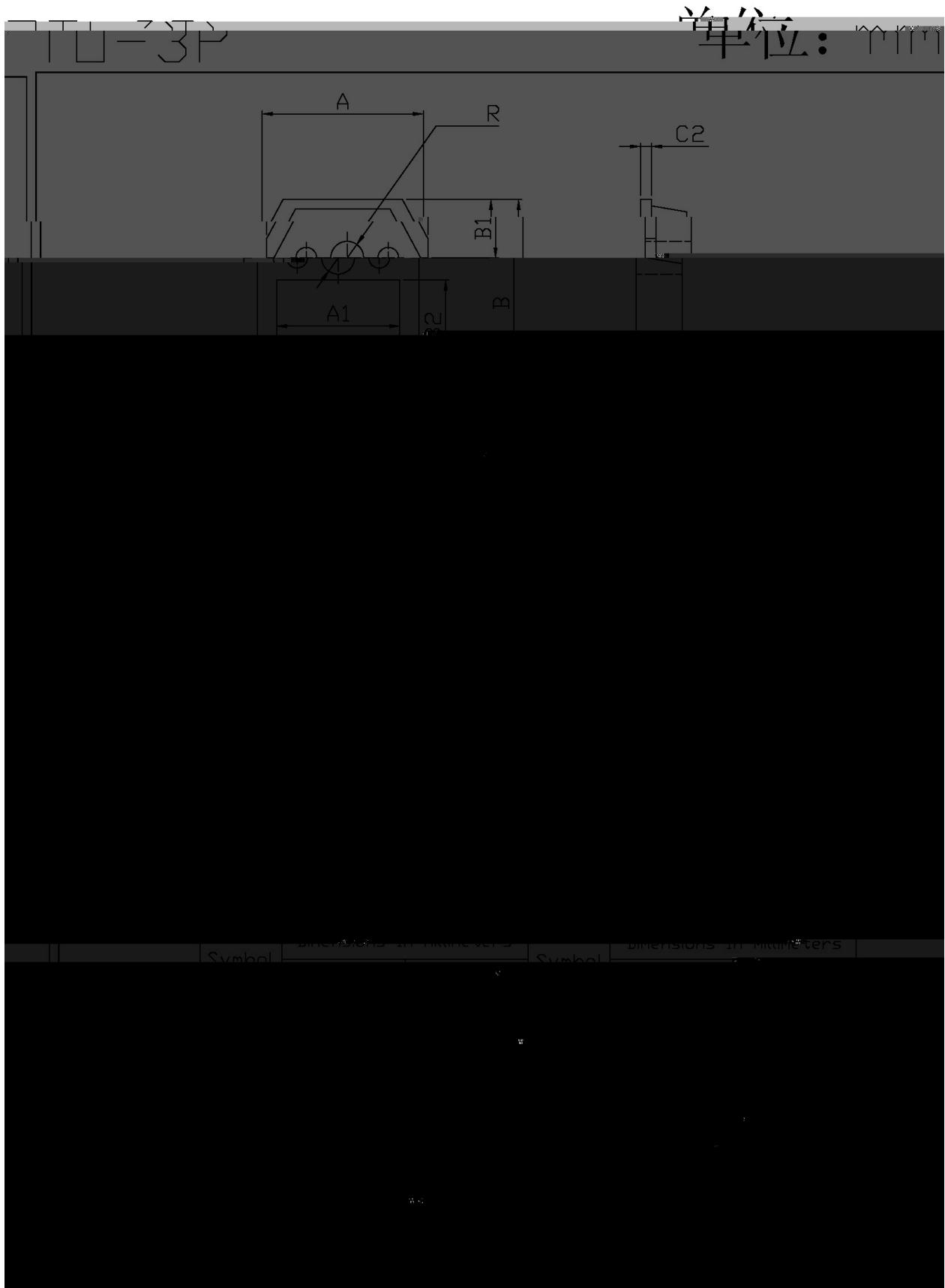
h_{FE} Classifications Symbol	R	O
h_{FE} Range	55~110	80~160

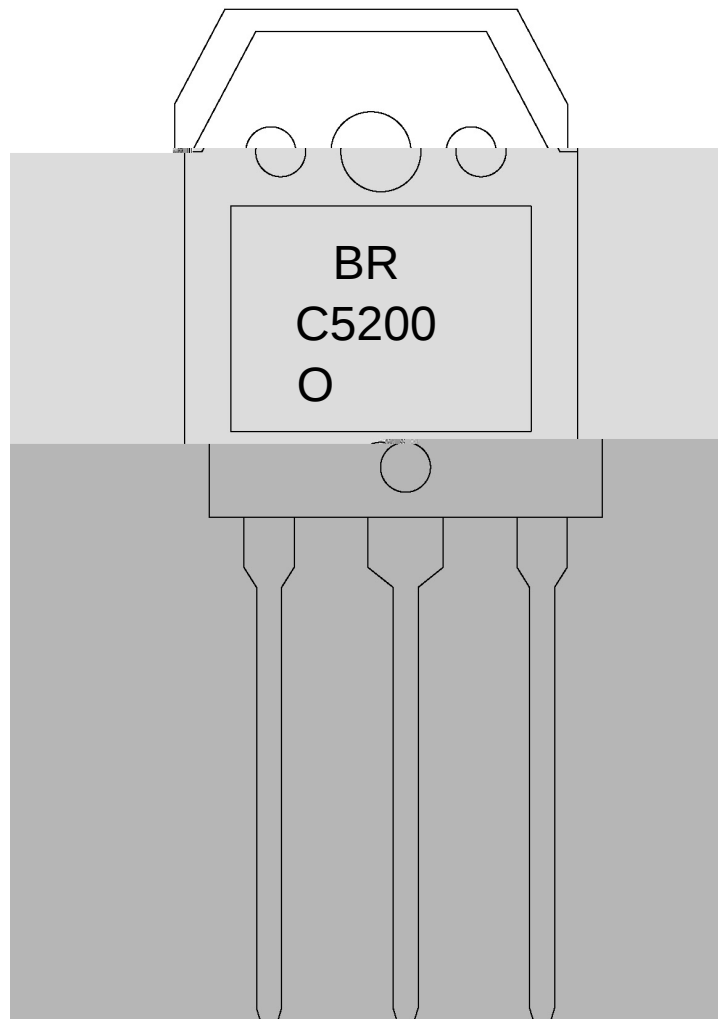
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	230	V
Collector to Emitter Voltage	V_{CEO}	230	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	15	A
Peak Collector Current	I_{CP}	30	A
Base Current	I_B	1.5	A
Collector Power Dissipation	$P_{C(TC=25^\circ)}$	150	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=50mA$ $I_B=0$	230			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=230V$ $I_E=0$			5	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			5	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5.0V$ $I_C=1.0A$	55		160	
	$h_{FE(2)}$	$V_{CE}=5.0V$ $I_C=7.0A$	35	60		
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=8.0A$ $I_B=0.8A$		0.4	3	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=5.0V$ $I_C=7.0A$		1	1.5	V
Transition Frequency	f_T	$V_{CE}=5.0V$ $I_C=1.0A$		30		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		200		pF

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h_{FE}

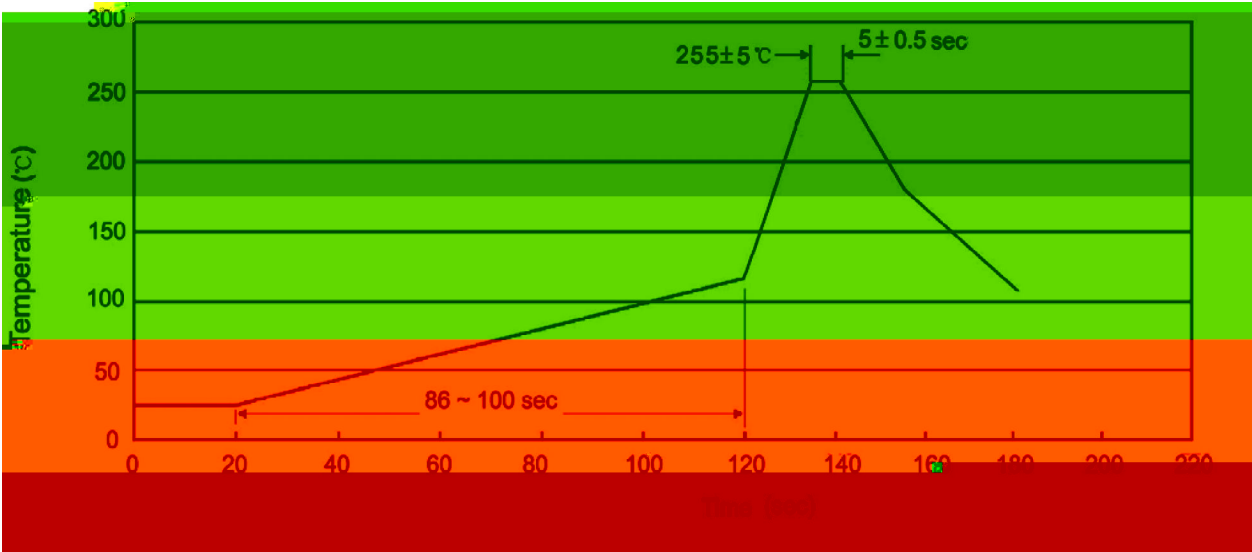
Note:

BR: Company Code.

C5200: Product Type.

O: h_{FE} Classifications Symbol.

***: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

270 5

10 1 sec.

Temp.:270±5

Time:10±1 sec

/ TUBE

Package Type	Units					Dimension		(unit mm ³)
								x x